



0039-7692-2S

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :
AKIRA GODA, ET AL. : GROUP ART UNIT: 2822
SERIAL NO: 09/556,777 :
RCE FILED: HEREWITH : EXAMINER: SOWARD, I.
FOR: NONVOLATILE SEMICONDUCTOR
MEMORY DEVICE AND METHOD
FOR MANUFACTURING THE SAME

#14/B
[Signature]

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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated July 3, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend Claims 1, 20, and 22 as shown in clean form below.¹

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1. (Twice Amended) A nonvolatile semiconductor memory device comprising:

a semiconductor substrate;

an element isolation region formed in the semiconductor substrate, the element isolation region isolating a plurality of element regions in the semiconductor substrate;

a first transistor formed in a peripheral circuit portion of the semiconductor substrate, the first transistor including source and drain diffusion layers formed in one of the plurality of element regions and a gate electrode having a first gate length;

¹A marked-up copy of the amended portion of the claims is attached hereto.

